

# One Watt High Current Transistors

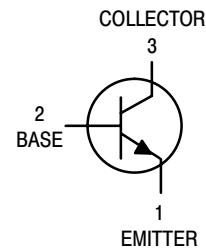
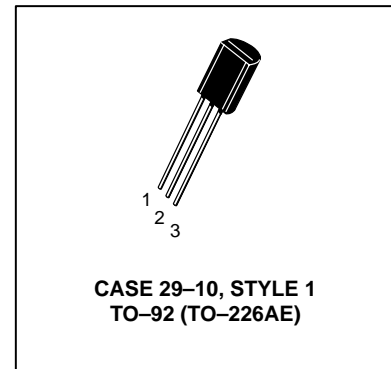
## NPN Silicon

### MPSW01 MPSW01A\*

\*ON Semiconductor Preferred Device

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MPSW01 MPSW01A	$V_{CEO}$	30 40	Vdc
Collector–Base Voltage MPSW01 MPSW01A	$V_{CBO}$	40 50	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current — Continuous	$I_C$	1000	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.0 8.0	Watts mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.5 20	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$



#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 10 \text{ mAdc}, I_E = 0$ )	MPSW01 MPSW01A	$V_{(BR)CEO}$	30 40	—	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu\text{Adc}, I_E = 0$ )	MPSW01 MPSW01A	$V_{(BR)CBO}$	40 50	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 100 \mu\text{Adc}, I_C = 0$ )		$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 40 \text{ Vdc}, I_E = 0$ )	MPSW01 MPSW01A	$I_{CBO}$	— —	0.1 0.1	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_C = 0$ )		$I_{EBO}$	—	0.1	$\mu\text{Adc}$

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MPSW01 MPSW01A

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS<sup>(1)</sup></b>				
DC Current Gain ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1000\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	55 60 50	— — —	—
Collector–Emitter Saturation Voltage ( $I_C = 1000\text{ mAdc}$ , $I_B = 100\text{ mAdc}$ )	$V_{CE(sat)}$	—	0.5	Vdc
Base–Emitter On Voltage ( $I_C = 1000\text{ mAdc}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$V_{BE(on)}$	—	1.2	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 20\text{ MHz}$ )	$f_T$	50	—	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	20	pF

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

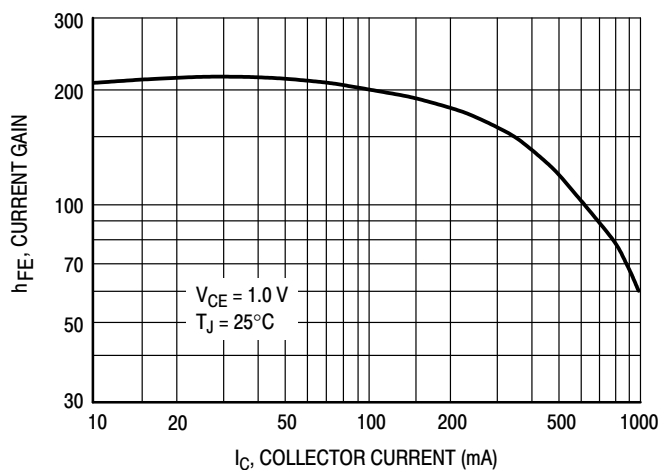


Figure 1. DC Current Gain

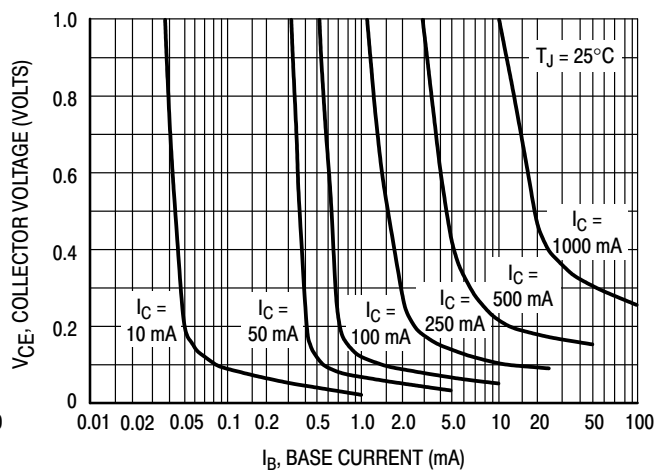


Figure 2. Collector Saturation Region

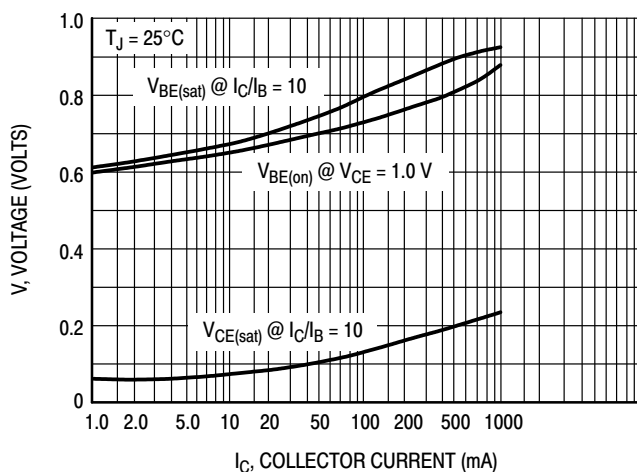


Figure 3. "ON" Voltages

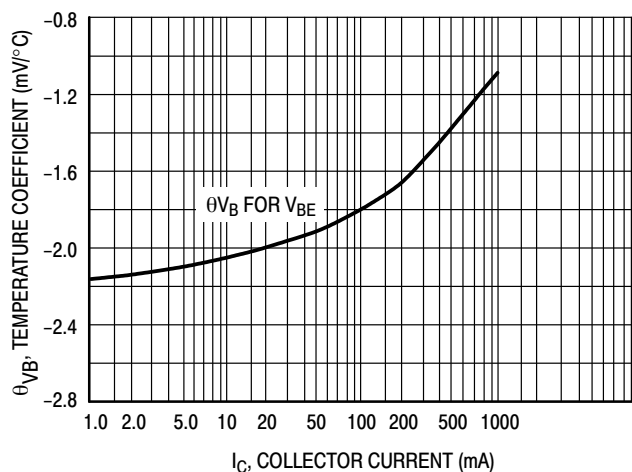


Figure 4. Temperature Coefficient

# MPSW01 MPSW01A

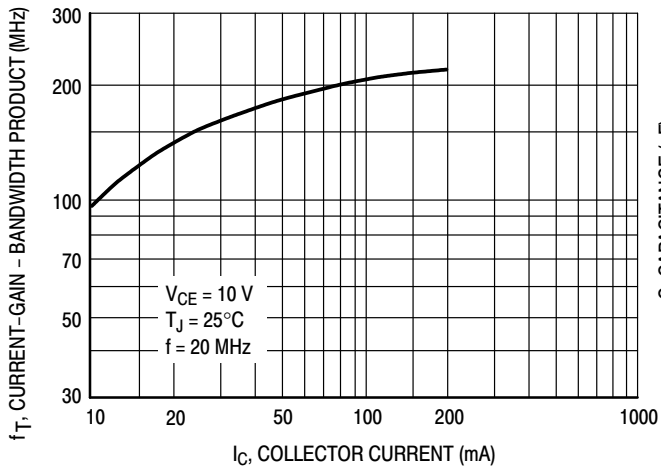


Figure 5. Current Gain — Bandwidth Product

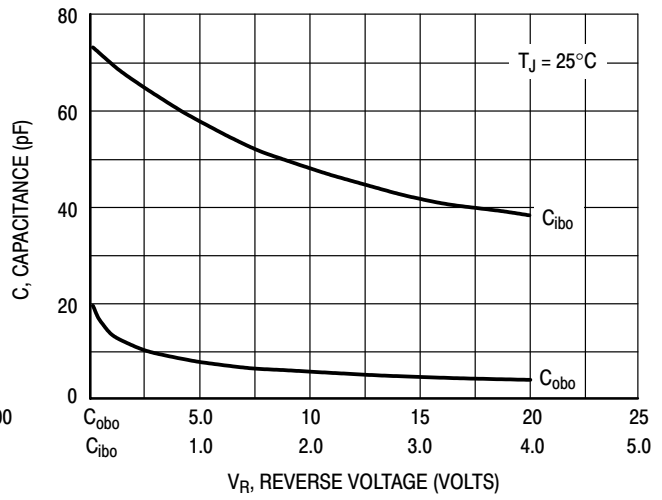


Figure 6. Capacitance

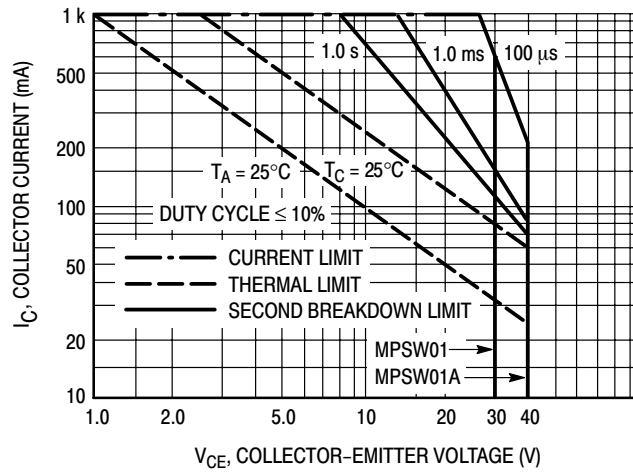
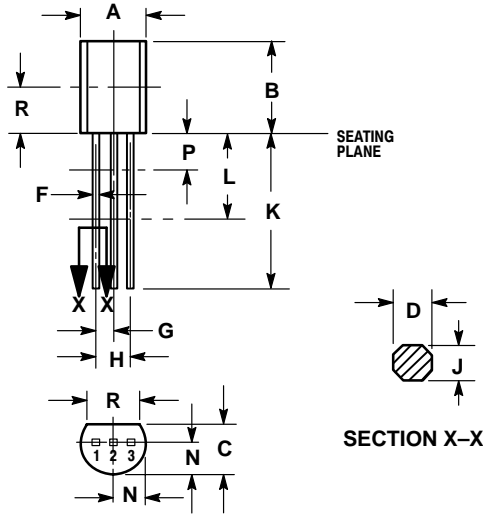


Figure 7. Active Region — Safe Operating Area

# MPSW01 MPSW01A

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-10  
ISSUE AL



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

### LE 5:

1. DRAIN
2. SOURCE
3. GATE

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